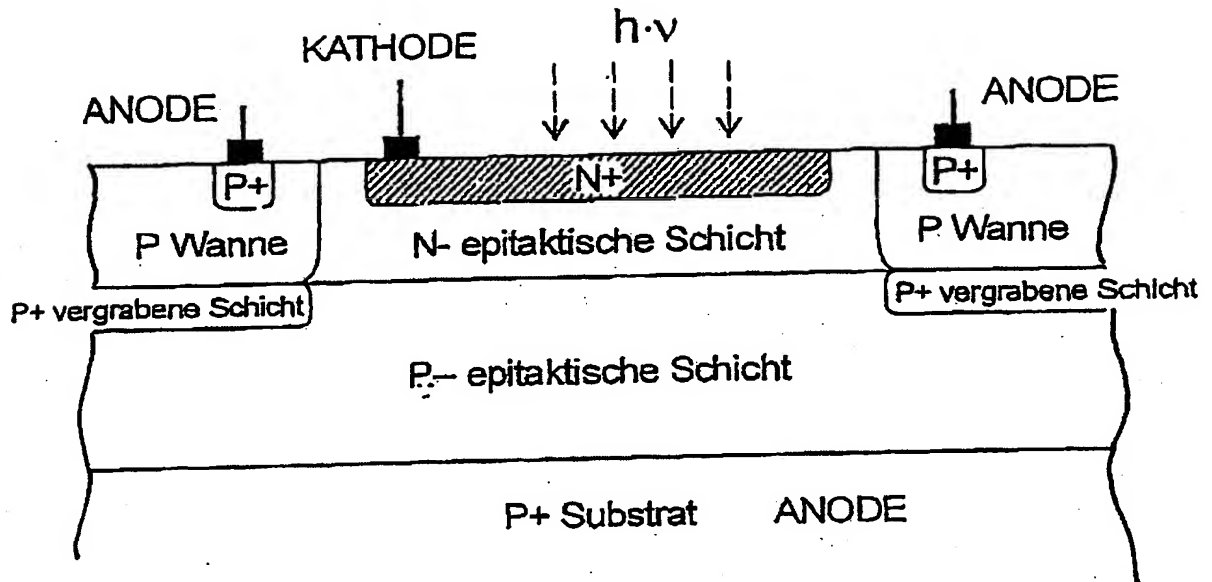


Figure 1



KEY:

ANODE - ANODE

KATHODE - CATHODE

P Wanne - P well

N- epitaktische Schicht - N epitactic layer

P+ vergrabene Schicht - P+ buried layer

P- epitaktische Schicht - P- epitactic layer

P+ Substrat - P+ substrate

Table 1

	Standard process		Modified process	
	670 nm	785 nm	670 nm	785 nm
Optical wavelength λ	670 nm	785 nm	670 nm	785 nm
Quantum efficiency η (%)	94.3	71.3	96.5	63.4
Sensitivity R (A/W)	0.508	0.450	0.520	0.400
Rise time t_R (nsec)	3.00	12.40	0.610	1.465
Fall time t_F (nsec)	6.50	10.40	0.515	1.480
3 dB band width NW (MHz)	79.3	30.8	625	238
Capacity C_D (fF/ μm^2)	0.134	0.134	0.0105	0.0105

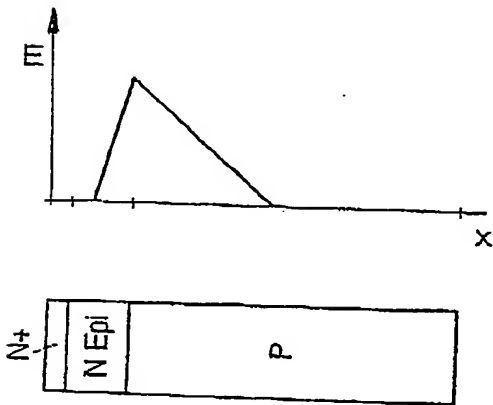
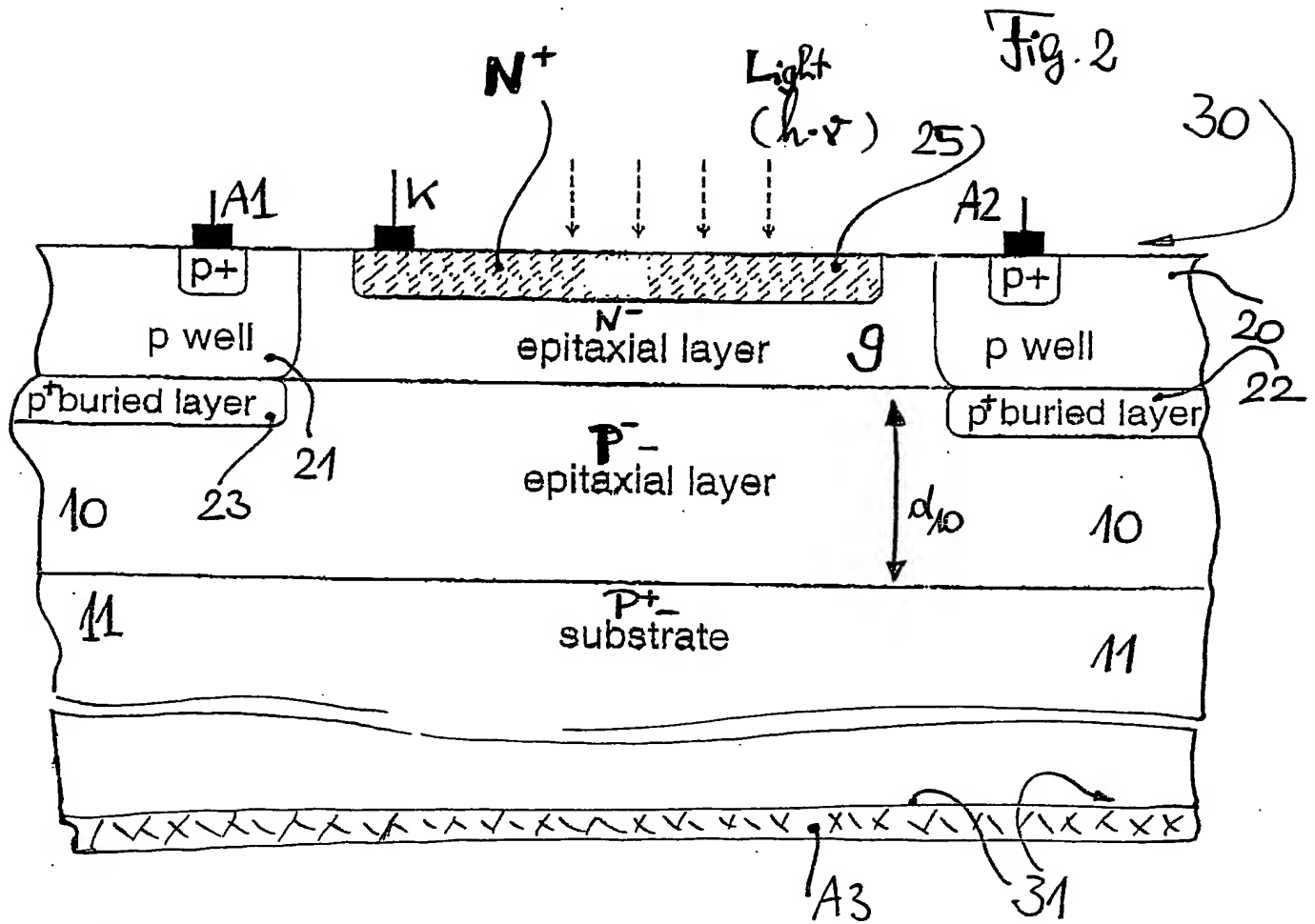


Fig. 3

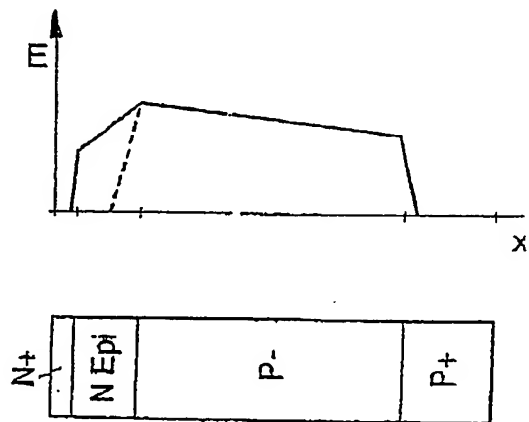


Fig. 4